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Diodes Incorporated DMN2114SN-7

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Datasheet of DMN2114SN-7 - MOSFET N-CH 20V 1.2A SC59-3

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com





DMN2114SN

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

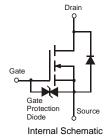
- Low On-Resistance
- Ideal for Notebook Computer, Portable Phone, PCMCIA Cards, and Battery Power Circuits
- Lead Free By Design/RoHS Compliant (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability
- **ESD Protected Gate**
- "Green" Device (Note 3)

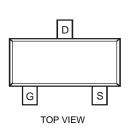
Mechanical Data

- Case: SC59
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.014 grams (approximate)









Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage Continuo	us V _{GSS}	±12	V
Drain Current Continuo Puls	- In	1.2 4.0	А

SC-59

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation	P _d	500	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	250	°C /W
Operating and Storage Temperature Range	T _i , T _{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Cumbal	Min	T	Max	I lesia	Toot Condition		
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 1)			1			_		
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current @ T _j =	25°C I _{DSS}	_	_	10	μΑ	$V_{DS} = 24V$, $V_{GS} = 0V$		
Gate-Body Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 1)			ā.			_		
Gate Threshold Voltage	V _{GS(th)}	0.7	_	1.40	V	$V_{DS} = 10V, I_D = 1.0mA$		
Static Drain-Source On-Resistance		_	_	0.100	0	$V_{GS} = 4.5V, I_D = 0.5A$		
Static Diani-Source Off-Resistance	R _{DS (ON)}	_	_	0.160	Ω	$V_{GS} = 2.5V, I_D = 0.5A$		
Forward Transfer Admittance	Y _{fs}	_	3.3		S	$V_{DS} = 10V, I_{D} = 0.5A$		
Diode Forward Voltage	V _{SD}	_	0.8	1.1	V	$V_{GS} = 0V, I_S = 1.0A$		
DYNAMIC CHARACTERISTICS		•	•					
Input Capacitance	C _{iss}	_	180		pF	10/1/		
Output Capacitance	Coss	_	120	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ -f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	_	45	_	pF	71 = 1.0WHZ		
SWITCHING CHARACTERISTICS								
Turn-On Delay Time	t _{D(ON)}	_	10		ns			
Turn-Off Delay Time	t _{D(OFF)}		50		ns	$V_{DD} = 10V, I_D = 0.5A,$		
Turn-On Rise Time	t _r	_	15	_	ns	$V_{GS} = 5.0V$, $R_{GEN} = 50\Omega$		
Turn-Off Fall Time	t _f	_	45	_	ns	1		

Notes:

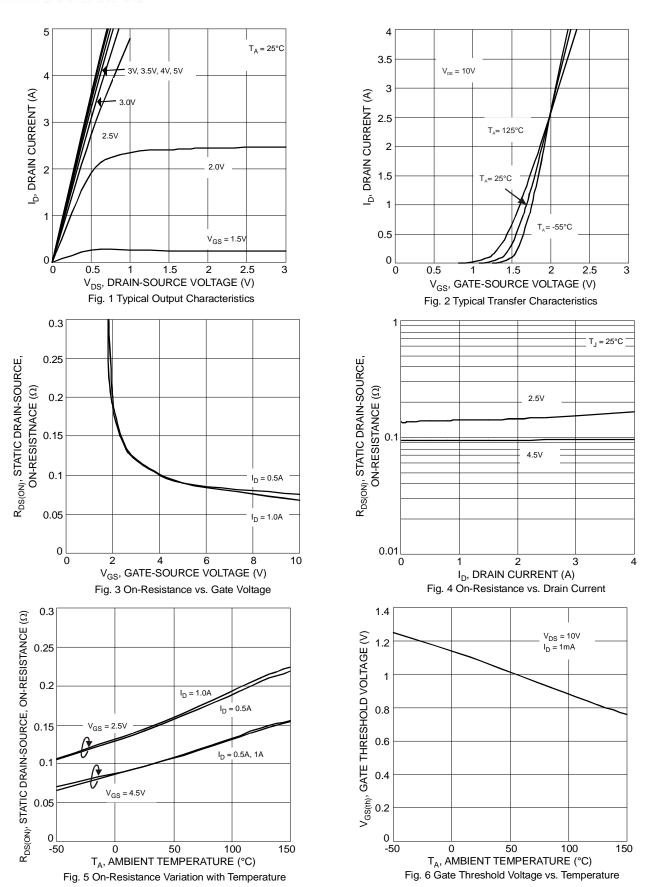
- Pulse width $\leq 300 \mu S$, duty cycle $\leq 2\%$.
- No purposefully added lead.
 Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

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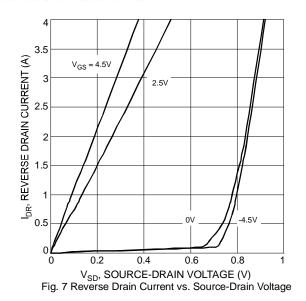


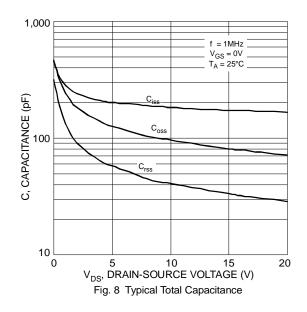
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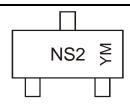


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2114SN-7	SC59	3000/Tape & Reel

Notes: 4. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

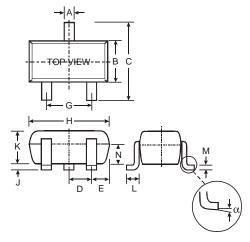


NS2 = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	V	V	Х		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SC59					
Dim	Min	Max			
Α	0.35	0.50			
В	1.50	1.70			
С	2.70	3.00			
D	0.0	95			
Е	_	_			
G	1.90				
Н	2.90	3.10			
7	0.013	0.10			
K	1.00	1.30			
L	0.35	0.55			
M	0.10	0.20			
N	0.70	0.80			
α	0°	8°			
All Di	All Dimensions in mm				

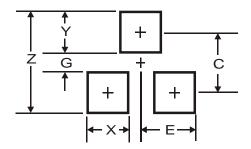
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DMN2114SN

Suggested Pad Layout



Dimensions	Value (in mm)
Z	4.0
G	1.2
X	0.9
Υ	1.4
С	2.6
E	0.95

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